

WHAT IS CLAIMED IS:

1. A metal wiring method for an undercut in a MEMS packaging process, the method comprising:
 - disposing a MEMS element on a silicon substrate;
 - welding a glass wafer to an upper portion of the silicon substrate having the MEMS element disposed thereon, the glass wafer having a hole formed therein for connecting a metal wiring;
 - depositing a thin metal film for the metal wiring in the hole; and
 - ion-mealing the deposited thin metal film.
2. The method as claimed in claim 1, wherein in the ion-mealing, the deposited thin metal film is resputtered by injecting accelerated gas particles to strike the deposited thin metal film.
3. The method as claimed in claim 2, wherein if the glass wafer has an undercut formed around the hole formed therein, the undercut is filled with the resputtered thin metal film.
4. The method as claimed in claim 3, wherein when the glass wafer has the undercut formed around the hole formed therein, the ion-mealing is performed until the undercut is removed.

5. The method as claimed in claim 2, wherein the accelerated gas particles are argon gas particles.